MJD41C (NPN)
MJD42C (PNP)

Preferred Device

Complementary Power Transistors

DPAK For Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves (“1” Suffix)
- Lead Formed Version in 16 mm Tape and Reel (“T4” Suffix)
- Electrically Similar to Popular TIP41 and TIP42 Series
- Monolithic Construction With Built−in Base − Emitter Resistors
- Epoxy Meets UL 94, V−0 @ 0.125 in.
- ESD Ratings: Human Body Model, 3B > 8000 V
  Machine Model, C > 400 V

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector−Emitter Voltage	V_{CEO}	100	Vdc
Collector−Base Voltage	V_{CB}	100	Vdc
Emitter−Base Voltage	V_{EB}	5	Vdc
Collector Current − Continuous Peak	I_C	6 10	Adc
Base Current	I_B	2	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	20 0.16	W W/°C
Total Power Dissipation* @ T_A = 25°C Derate above 25°C	P_D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance, Junction−to−Ambient*	$R_{\theta JA}$	71.4	°C/W

*These ratings are applicable when surface mounted on the minimum pad sizes recommended.

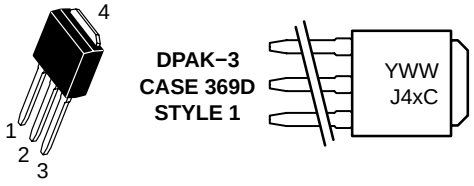
ON Semiconductor®

http://onsemi.com

SILICON
POWER TRANSISTORS
6 AMPERES
100 VOLTS
20 WATTS

MARKING DIAGRAMS

DPAK
CASE 369C
STYLE 1



DPAK−3
CASE 369D
STYLE 1

Y = Year
WW = Work Week
x = 1 or 2

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Sustaining Voltage (Note 1) (I_C = 30 mAdc, I_B = 0)	$V_{CEO(sus)}$	100	−	Vdc
Collector Cutoff Current (V_{CE} = 60 Vdc, I_B = 0)	I_{CEO}	−	50	μAdc
Collector Cutoff Current (V_{CE} = 100 Vdc, V_{EB} = 0)	I_{CES}	−	10	μAdc
Emitter Cutoff Current (V_{BE} = 5 Vdc, I_C = 0)	I_{EBO}	−	0.5	mAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain (I_C = 0.3 Adc, V_{CE} = 4 Vdc) (I_C = 3 Adc, V_{CE} = 4 Vdc)	h_{FE}	 30 15	 − 75	−
Collector−Emitter Saturation Voltage (I_C = 6 Adc, I_B = 600 mAdc)	$V_{CE(sat)}$	−	1.5	Vdc
Base−Emitter On Voltage (I_C = 6 Adc, V_{CE} = 4 Vdc)	$V_{BE(on)}$	−	2	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain − Bandwidth Product (Note 2) (I_C = 500 mAdc, V_{CE} = 10 Vdc, f_{test} = 1 MHz)	f_T	3	−	MHz
Small−Signal Current Gain (I_C = 0.5 Adc, V_{CE} = 10 Vdc, f = 1 kHz)	h_{fe}	20	—	−

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. $f_T = |h_{fe}| \bullet f_{test}$.

ORDERING INFORMATION

Device	Package Type	Package	Shipping†
MJD41CRL	DPAK	369C	1800 Tape & Reel
MJD41CT4	DPAK	369C	2500 Tape & Reel
MJD42C	DPAK	369C	75 Units / Rail
MJD42C1	DPAK−3	369D	75 Units / Rail
MJD42CRL	DPAK	369C	1800 Tape & Reel
MJD42CT4	DPAK	369C	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

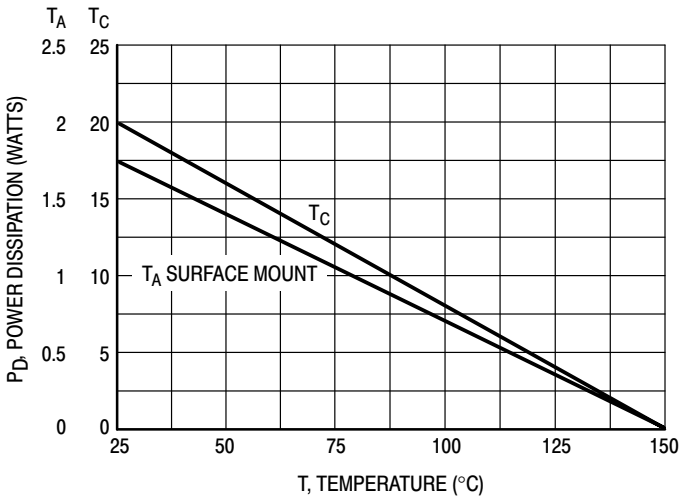
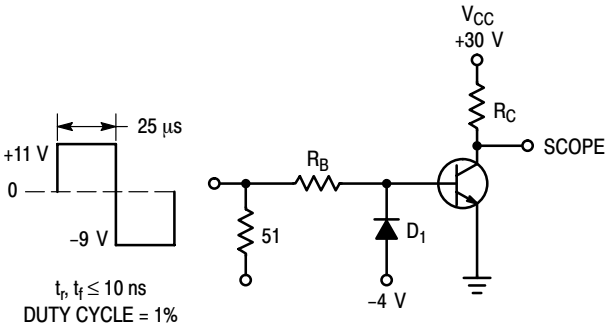


Figure 1. Power Derating



R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS
D_1 MUST BE FAST RECOVERY TYPE, e.g.:
MSB5300 USED ABOVE $I_B \approx 100$ mA
MSD6100 USED BELOW $I_B \approx 100$ mA
REVERSE ALL POLARITIES FOR PNP.

Figure 2. Switching Time Test Circuit

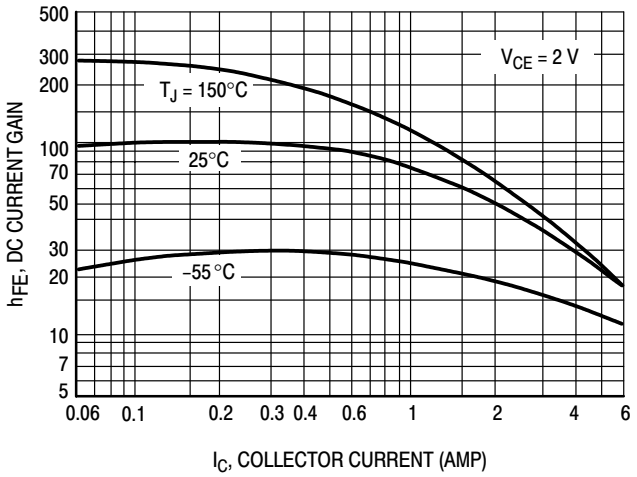


Figure 3. DC Current Gain

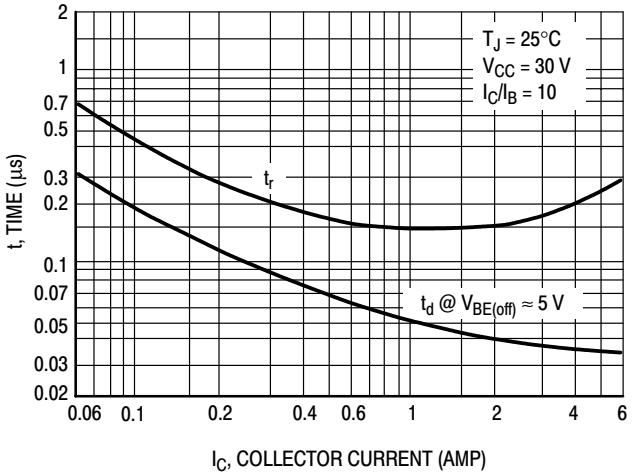


Figure 4. Turn−On Time

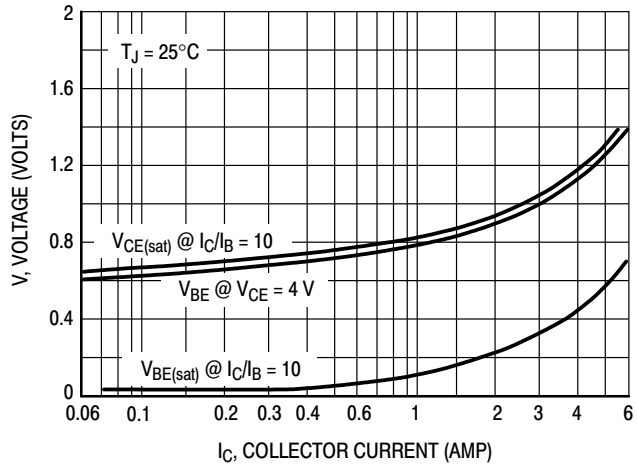


Figure 5. “On” Voltages

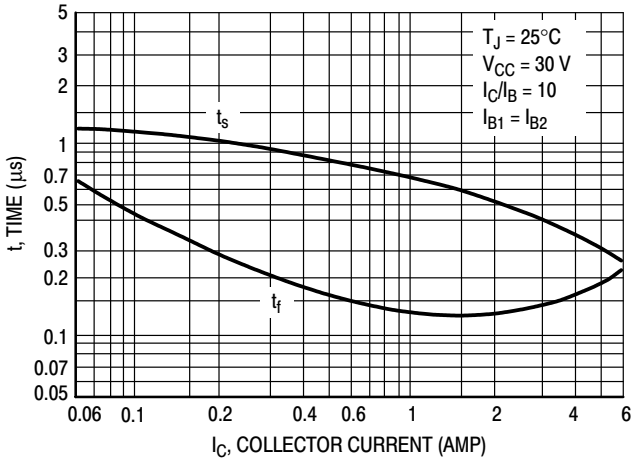


Figure 6. Turn−Off Time

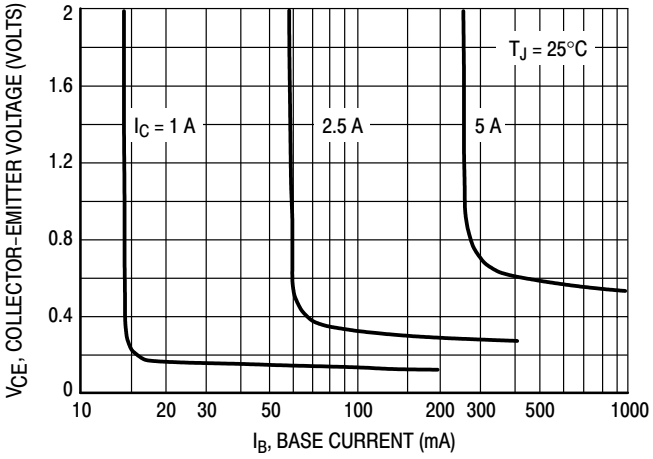


Figure 7. Collector Saturation Region

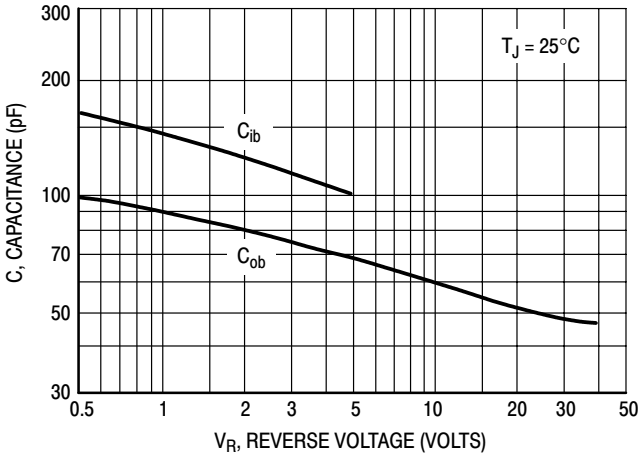


Figure 8. Capacitance

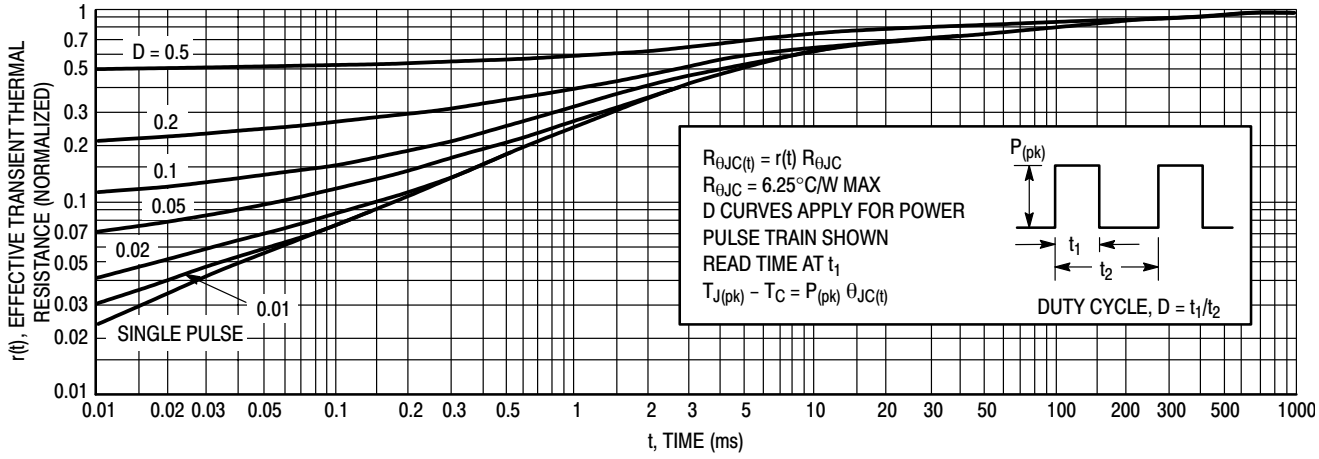


Figure 9. Thermal Response

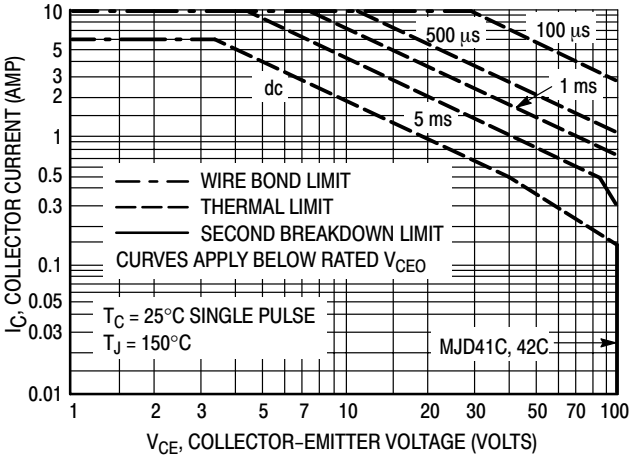


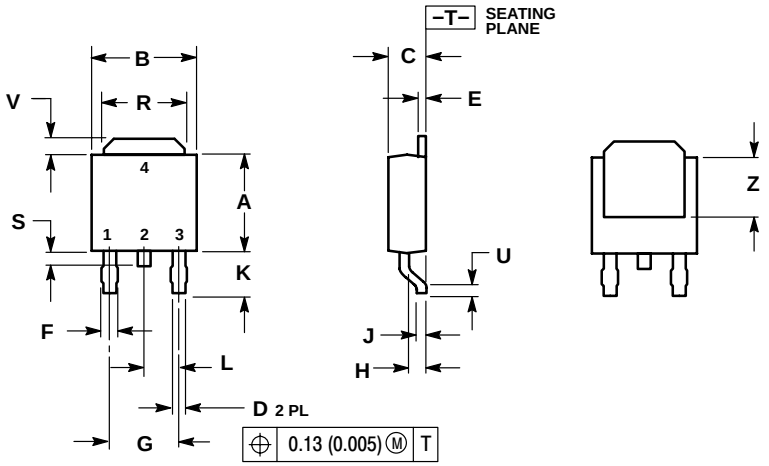
Figure 10. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 10 is based on $T_{J(pk)}$ = 150°C; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 9. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

PACKAGE DIMENSIONS

DPAK
CASE 369C
ISSUE O

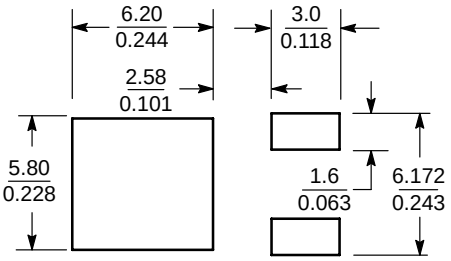


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

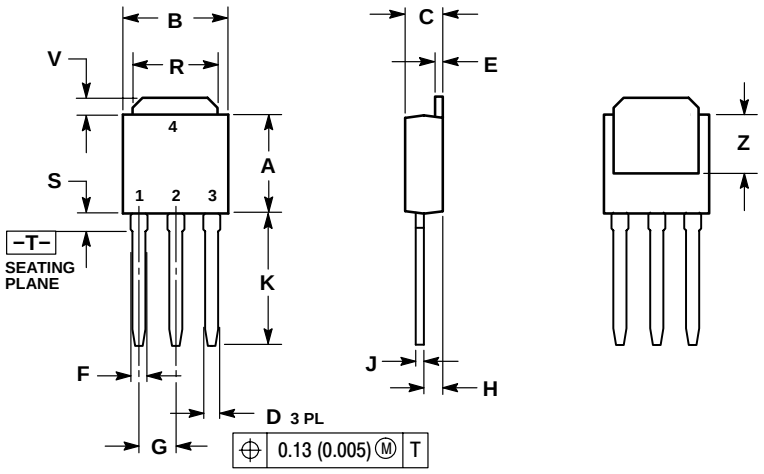
SOLDERING FOOTPRINT



SCALE 3:1 (mm / inches)

PACKAGE DIMENSIONS

DPAK−3
CASE 369D−01
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
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A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	−−−	3.93	−−−

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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MJD41C/D